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2SB0766G

Silicon PNP epitaxial planar type

For low-frequency output amplification Complementary to 2SD0874G

Features

- Large collector power dissipation P_C
- Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing

■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V _{CBO}	-60	V	
Collector-emitter voltage (Base open)	V _{CEO}	-50	V	
Emitter-base voltage (Collector open)	V _{EBO}	-5	V	
Collector current	I_{C}	-1	A	
Peak collector current	I _{CP}	-1.5	A	
Collector power dissipation *	$P_{\rm C}$	1	W	
Junction temperature	T_{j}	150	°C	
Storage temperature	T _{stg}	-55 to +150	°C	

Package

- Code
 - MiniP3-F2
- Pin Name
 - 1: Base
 - 2: Collector
 - 3: Emitter
- Marking Symbol: B

Note) *: Print circuit board: Copper foil area of 1 cm² or more, and the board thickness of 1.7 mm for the collector portion.

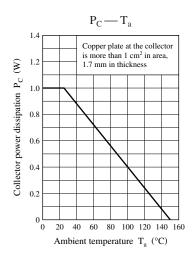
■ Electrical Characteristics $T_a = 25$ °C ± 3°C

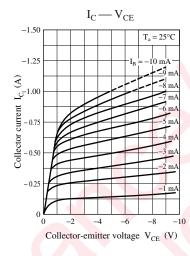
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_C = -10 \mu\text{A}, I_E = 0$		c0/,		V
Collector-emitter voltage (Base open)	V _{CEO}	$I_{\rm C} = -2 \text{ mA}, I_{\rm B} = 0$		0.		V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = -10 \mu A, I_C = 0$				V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = -20 \text{ V}, I_{E} = 0$			- 0.1	μΑ
Forward current transfer ratio *1	h _{FE1} *2	$V_{CE} = -10 \text{ V}, I_{C} = -500 \text{ mA}$	85		340	_
C _S ,	h _{FE2}	$V_{CE} = -5 \text{ V}, I_{C} = -1 \text{ A}$	50			
Collector-emitter saturation voltage *1	V _{CE(sat)}	$I_C = -500 \text{ mA}, I_B = -50 \text{ mA}$		- 0.2	- 0.4	V
Base-emitter saturation voltage *1	V _{BE(sat)}	$I_C = -500 \text{ mA}, I_B = -50 \text{ mA}$		- 0.85	-1.20	V
Transition frequency	f_T	$V_{CB} = -10 \text{ V}, I_E = 50 \text{ mA}, f = 200 \text{ MHz}$		200		MHz
Collector output capacitance (Common base, input open circuited)	C _{ob}	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		20	30	pF

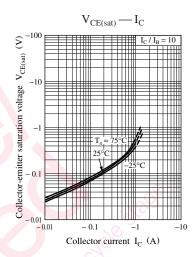
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

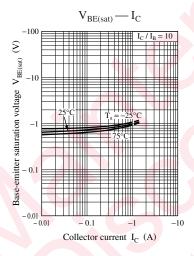
- 2. *1: Pulse measurement
 - *2: Rank classification

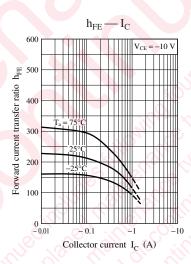
Rank	Q	R	S
h_{FE1}	85 to 170	120 to 240	170 to 340

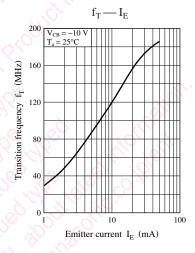


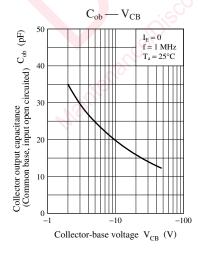


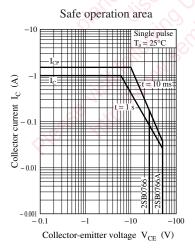






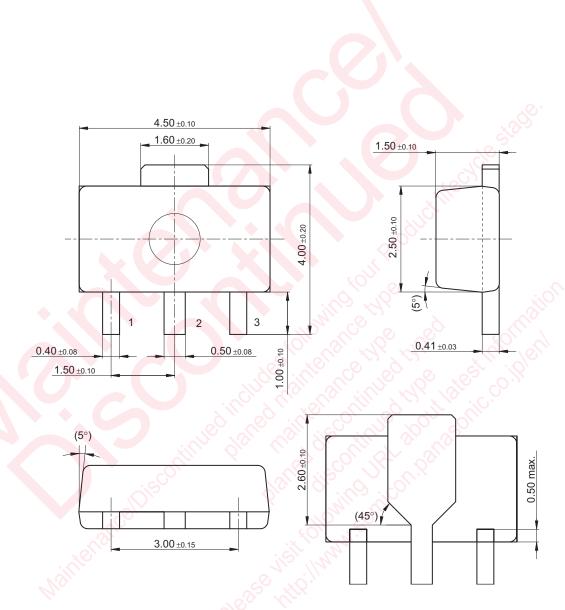






2 SJD00328AED

MiniP3-F2 Unit: mm



SJD00328AED 3

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